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FDG6318P

Dual P-Channel, Digital FET

General Description

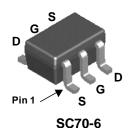
These dual P-Channel logic level enhancement mode MOSFET are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance. This device has been designed especially for low voltage applications as a replacement for bipolar digital transistors and small signal MOSFETS.

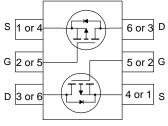
Applications

· Battery management

Features

- -0.5 A, -20 V. $R_{DS(ON)} = 780 \text{ m}\Omega$ @ $V_{GS} = -4.5 \text{ V}$ $R_{DS(ON)} = 1200 \text{ m}\Omega$ @ $V_{GS} = -2.5 \text{ V}$
- Very low level gate drive requirements allowing direct operation in 3V circuits (V_{GS(th)} < 1.5V).
- Compact industry standard SC70-6 surface mount package





The pinouts are symmetrical; pin 1 and pin 4 are interchangeable.

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-20	V
V _{GSS}	Gate-Source Voltage		±12	V
I _D	Drain Current - Continuous	(Note 1)	-0.5	Α
	– Pulsed		-1.8	
P _D	Power Dissipation for Single Operation	(Note 1)	0.3	W
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1)	415	°C/W
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Package Marking and Ordering Information

 Device Marking	Device	Reel Size	Tape width	Quantity
 .38	FDG6318P	7"	8mm	3000 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	acteristics					I.
BV _{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{D} = -250 \mu\text{A}$	-20			V
<u>ΔBV_{DSS}</u> ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu A$, Referenced to $25^{\circ}C$		-10		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
I _{GSS}	Gate-Body Leakage	$V_{GS} = \pm 12 \text{ V}, \ V_{DS} = 0 \text{ V}$			±100	nA
On Chara	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-0.65	-1.2	-1.5	V
$\Delta V_{GS(th)} \over \Delta T_{J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$, Referenced to 25°C		2		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$\begin{split} &V_{GS} = -4.5 \text{ V}, \ I_D = -0.5 \text{ A} \\ &V_{GS} = -2.5 \text{ V}, \ I_D = -0.4 \text{ A} \\ &V_{GS} = -4.5 \text{ V}, \ I_D = -0.5 \text{ A}, \ T_J = 125 ^{\circ}\text{C} \\ &V_{GS} = -4.5 \text{ V}, \ V_{DS} = -5 \text{ V} \end{split}$		580 980 780	780 1200	mΩ
I _{D(on)}	On–State Drain Current	$V_{GS} = -4.5 \text{ V}, \ V_{DS} = -5 \text{ V}$	-1.8			Α
g _{FS}	Forward Transconductance	$V_{DS} = -5 \text{ V}, I_{D} = -0.5 \text{ A}$		1.1		S
Dynamic	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$		83		pF
Coss	Output Capacitance	f = 1.0 MHz		20		pF
Crss	Reverse Transfer Capacitance			11		pF
₹ _G	Gate Resistance	$V_{GS} = 15 \text{ mV}, f = 1.0 \text{ MHz}$		12.1		Ω
Switching	g Characteristics (Note 2)					
d(on)	Turn-On Delay Time	$V_{DD} = -10 \text{ V}, I_{D} = 1 \text{ A},$		6	12	ns
r	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		12	22	ns
d(off)	Turn-Off Delay Time			6	13	ns
f	Turn-Off Fall Time			1	3	ns
Q_g	Total Gate Charge	$V_{DS} = -10 \text{ V}, I_{D} = -0.6 \text{ A},$		0.86	1.2	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -4.5 \text{ V}$		0.22		nC
Q_{gd}	Gate-Drain Charge			0.25		nC
Drain-So	urce Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Sour				-0.25	Α
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \qquad I_S = -0.25 \text{ A}(\text{Note 2})$		-0.83	-1.2	V
t _{rr}	Reverse Recovery Time	$I_F = -0.5 \text{ A},$		12.6		ns
Q _{rr}	Reverse Recovery Charge	$d_{iF}/d_{t} = 100 \text{ A/}\mu\text{s}$		2.52		nC

Notes

^{1.} $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design. $R_{\theta JA} = 415^{\circ}$ C/W when mounted on a minimum pad.

^{2.} Pulse Test: Pulse Width < 300μ s, Duty Cycle < 2.0%

Typical Characteristics

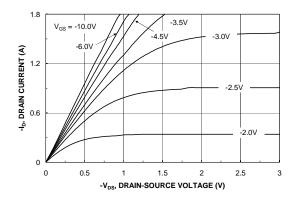


Figure 1. On-Region Characteristics.

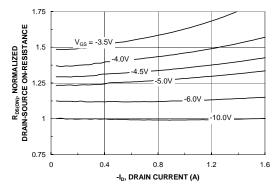


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

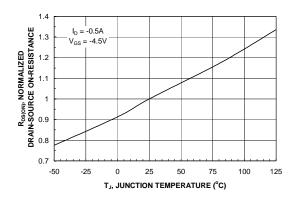


Figure 3. On-Resistance Variation with Temperature.

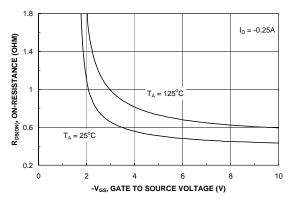


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

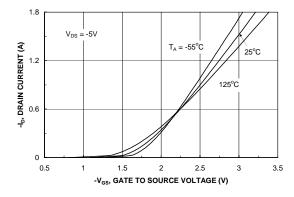


Figure 5. Transfer Characteristics.

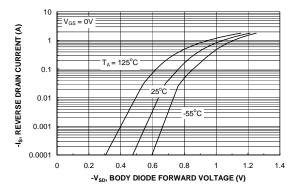
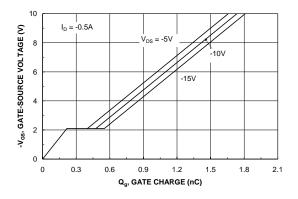


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



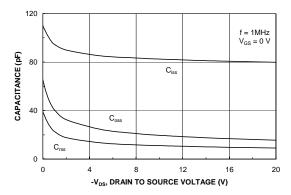
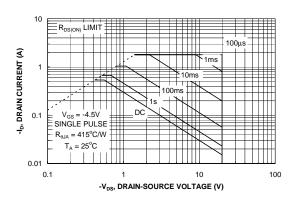


Figure 7. Gate Charge Characteristics.





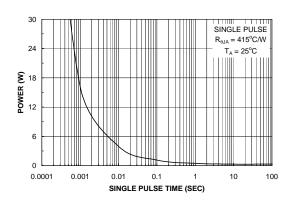


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

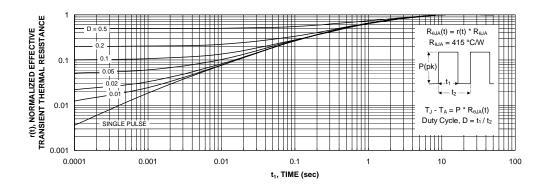


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1. Transient thermal response will change depending on the circuit board design.

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